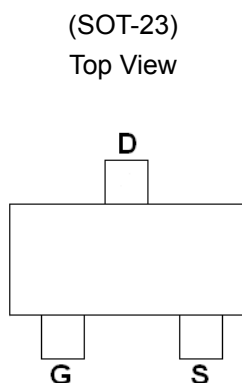


N-Channel 20V(D-S) MOSFET,ESD Protected

GENERAL DESCRIPTION

The ME2302D is the N-Channel logic enhancement mode power field effect transistors, using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone, notebook computer power management and other battery powered circuits, and low in-line power loss that are needed in a very small outline surface mount package.

PIN CONFIGURATION

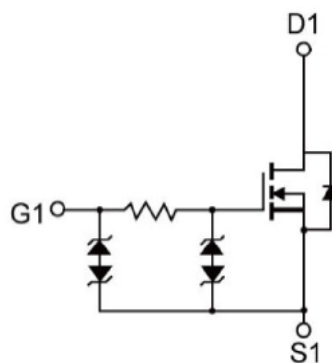


FEATURES

- $R_{DS(ON)} \leq 85m\Omega @ V_{GS}=4.5V$
- $R_{DS(ON)} \leq 115m\Omega @ V_{GS}=2.5V$
- $R_{DS(ON)} \leq 130m\Omega @ V_{GS}=1.8V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

APPLICATIONS

- Power Management in Notebook
- Portable Equipment
- Load Switch
- DSC



N-Channel MOSFET

Ordering Information: ME2302D (Pb-free)

ME2302D-G (Green product-Halogen free)

Absolute Maximum Ratings ($T_A=25^\circ C$ Unless Otherwise Noted)

Parameter	Symbol	Maximum Ratings	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	$T_A=25^\circ C$	A
		$T_A=70^\circ C$	
Pulsed Drain Current	I_{DM}	13	
Maximum Power Dissipation	P_D	$T_A=25^\circ C$	W
		$T_A=70^\circ C$	
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Maximum Junction-to-Ambient	R_{thJA}	90	$^\circ C/W$

*The device mounted on 1in² FR4 board with 2 oz copper



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Electrical Characteristics (T_A=25°C Unless Otherwise Specified)

Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC PARAMETERS						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μA	20			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250 μA	0.6		1.2	
I _{GSS}	Gate-Body Leakage Current	V _{DS} =0V, V _{GS} =±12V			±15	μA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V			1	μA
R _{DS(ON)}	Drain-Source On-Resistance	V _{GS} =4.5V, I _D = 2.8A		55	85	mΩ
		V _{GS} =2.5V, I _D = 2.5A		65	115	
		V _{GS} =1.8V, I _D = 2.2A		80	130	
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.75	1.2	V
DYNAMIC PARAMETERS						
Q _g	Total Gate Charge	V _{DS} =10V, V _{GS} =4.5V, I _D =2.8A		5		nC
Q _{gs}	Gate-Source Charge			1.6		
Q _{gd}	Gate-Drain Charge			1.4		
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz		316		pF
C _{oss}	Output Capacitance			50.7		
C _{rss}	Reverse Transfer Capacitance			36.7		
t _{d(on)}	Turn-On Delay Time	V _{DD} =10V, R _L =10Ω V _{GEN} =4.5Ω, R _G =6Ω		17.3		ns
t _r	Rise Time			22.5		
t _{d(off)}	Turn-Off Delay Time			107		
t _f	Fall Time			36.7		

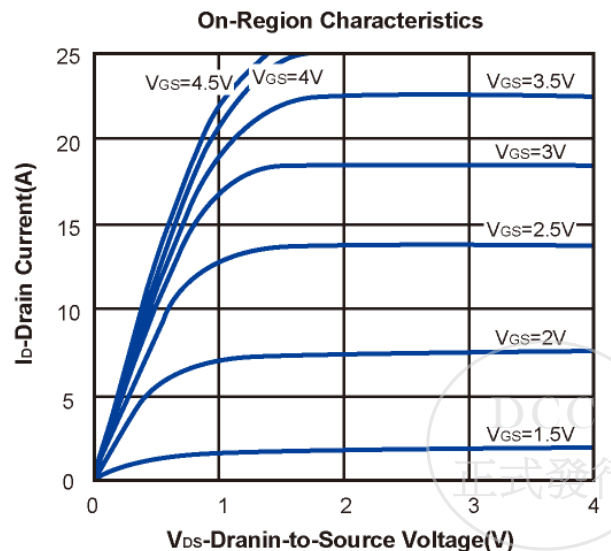
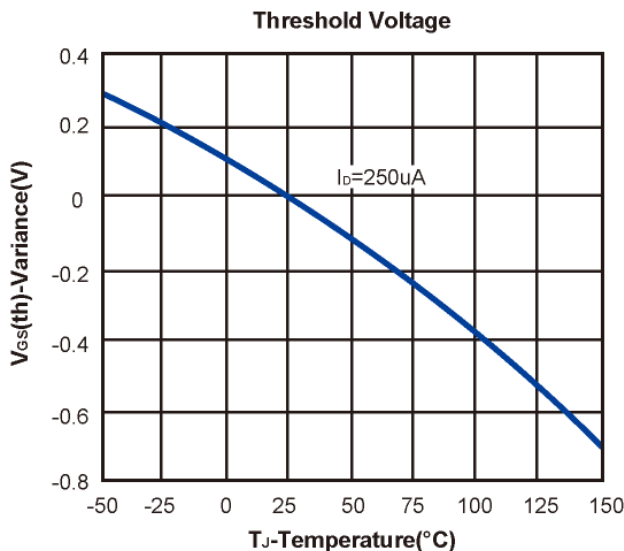
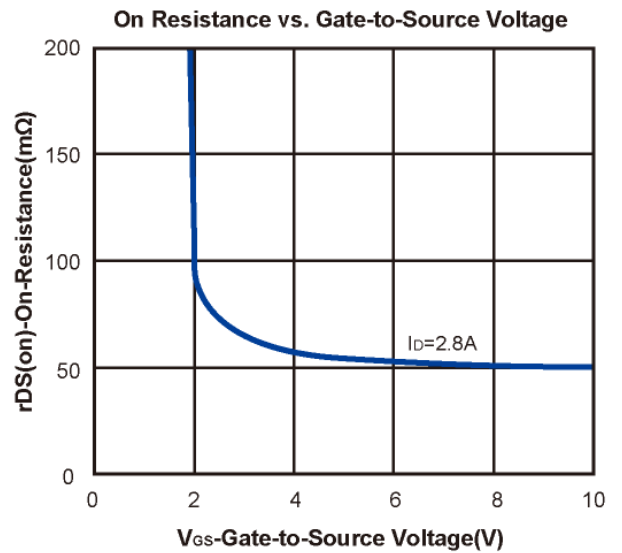
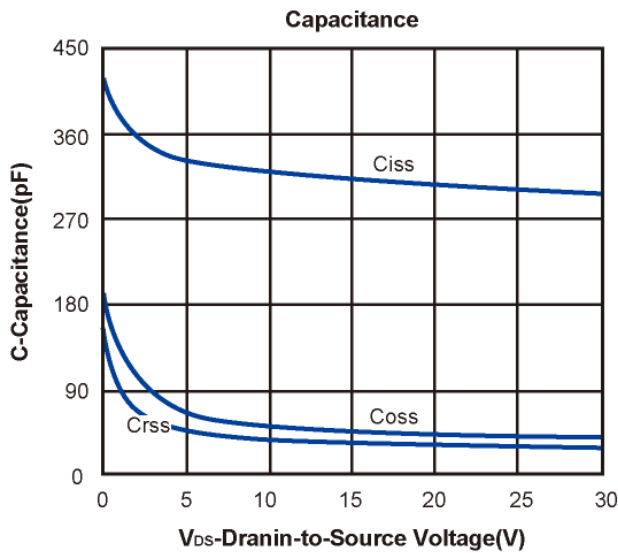
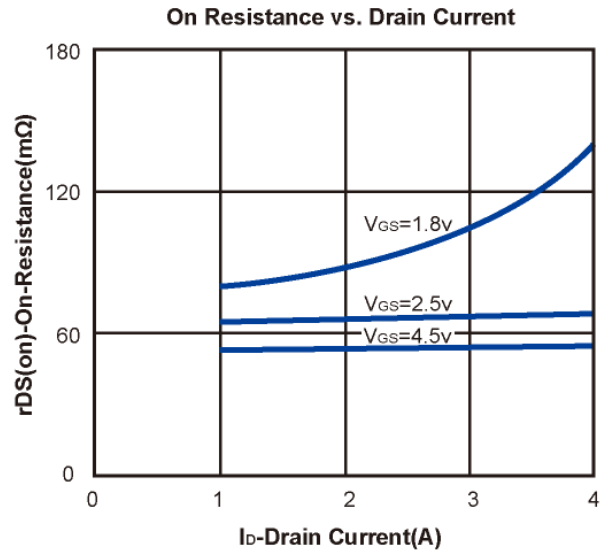
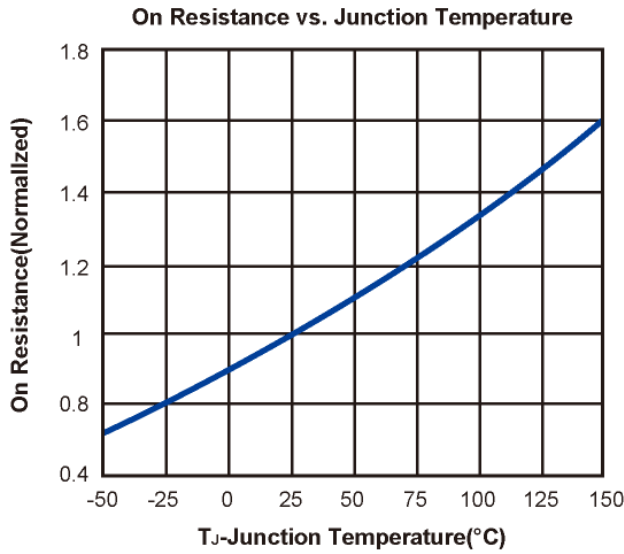
Notes: a. Pulse test; pulse width ≤ 380us, duty cycle ≤ 2%

b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.



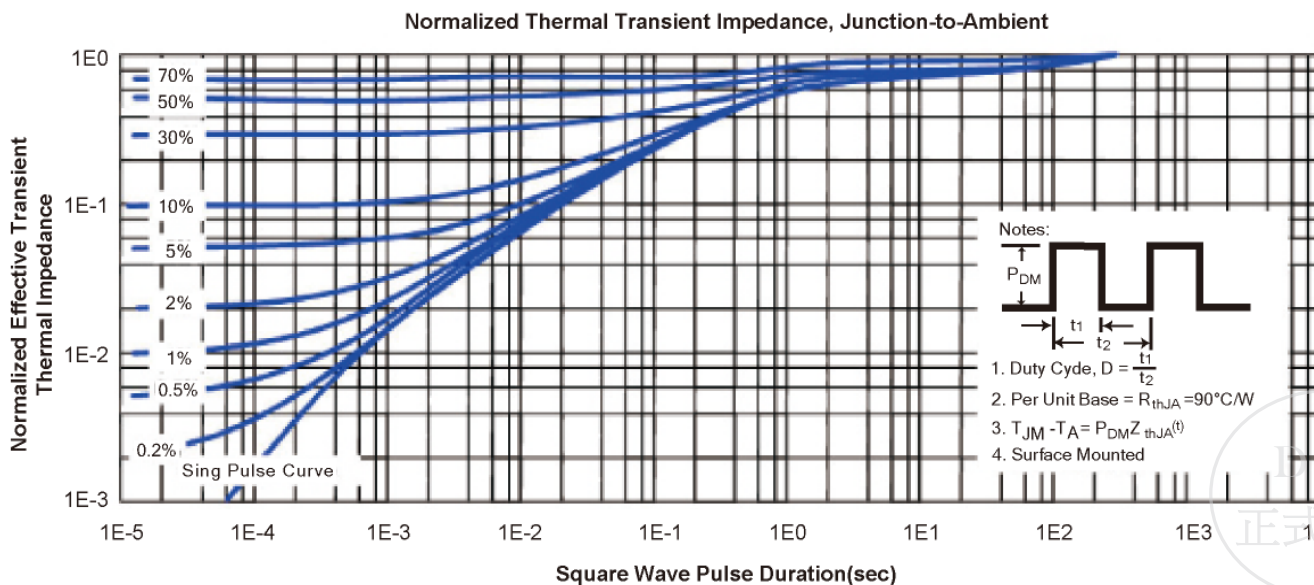
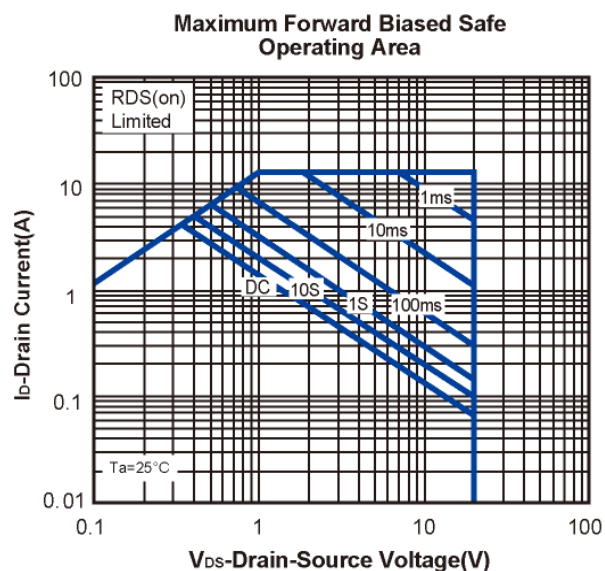
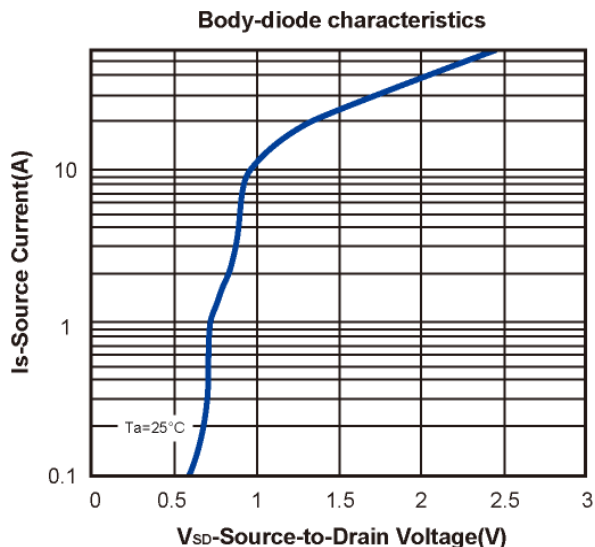
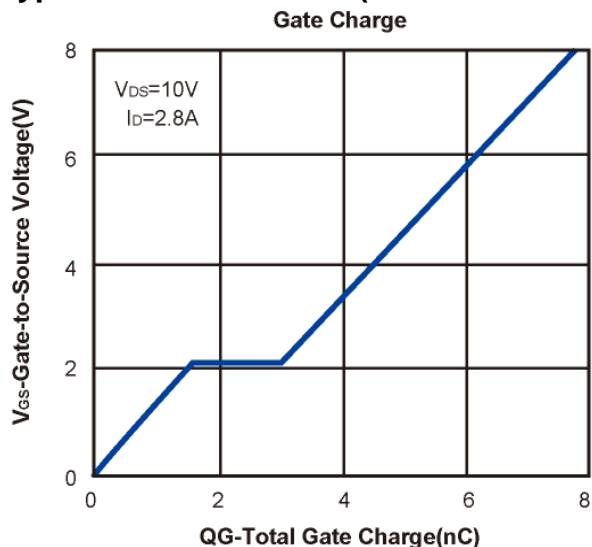
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Typical Characteristics (T_J =25°C Noted)

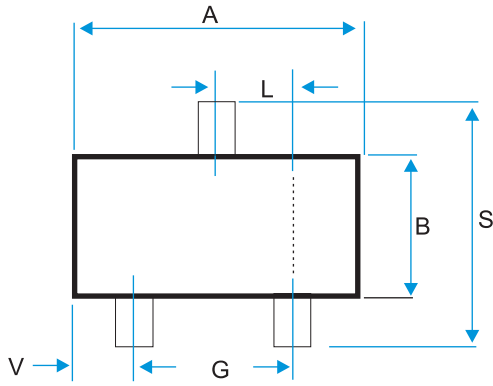


N-Channel 20V(D-S) MOSFET,ESD Protected

Typical Characteristics (T_J =25°C Noted)



SOT-23 Package Outline



DIM	MILLIMETERS (mm)	
	MIN	MAX
A	2.800	3.00
B	1.200	1.70
C	0.900	1.30
D	0.350	0.50
G	1.780	2.04
H	0.010	0.15
J	0.085	0.20
K	0.300	0.65
L	0.890	1.02
S	2.100	3.00
V	0.450	0.60

